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Kind regards,

Team Nexperia

PEMB9; PUMB9

PNP/PNP resistor-equipped transistors; R1 = 10 k Ω , R2 = 47 k Ω

Rev. 3 — 22 November 2011

Product data sheet

1. Product profile

1.1 General description

PNP/PNP double Resistor-Equipped Transistors (RET) in Surface-Mounted Device (SMD) plastic packages.

Table 1. Product overview

Type number			NPN/PNP	NPN/NPN	Package	
	NXP	JEITA	complement	complement	configuration	
PEMB9	SOT666	-	PEMD9	РЕМН9	ultra small and flat lead	
PUMB9	SOT363	SC-88	PUMD9	PUMH9	very small	

1.2 Features and benefits

- 100 mA output current capability
- Built-in bias resistors
- Simplifies circuit design
- Reduces component count
- Reduces pick and place costs
- AEC-Q101 qualified

1.3 Applications

- Low current peripheral driver
- Control of IC inputs
- Replaces general-purpose transistors in digital applications

1.4 Quick reference data

Table 2. Quick reference data

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Per transis	tor					
V_{CEO}	collector-emitter voltage	open base	-	-	-50	V
Io	output current		-	-	-100	mA
R1	bias resistor 1 (input)		7	10	13	kΩ
R2/R1	bias resistor ratio		3.7	4.7	5.7	



2. Pinning information

Table 3. Pinning

Pin	Description	Simplified outline	Graphic symbol
1	GND (emitter) TR1		
2	input (base) TR1	[6] [5] [4]	6 5 4
3	output (collector) TR2		
4	GND (emitter) TR2		R1 R2
5	input (base) TR2		TR1
6	output (collector) TR1	001aab555	R2 R1
			1 2 3
			006aaa21

3. Ordering information

Table 4. Ordering information

Type number	Package	Package		
	Name	Description	Version	
PEMB9	-	plastic surface-mounted package; 6 leads	SOT666	
PUMB9	SC-88	plastic surface-mounted package; 6 leads	SOT363	

4. Marking

Table 5. Marking codes

Type number	Marking code ^[1]
PEMB9	Z6
PUMB9	B*9

[1] * = placeholder for manufacturing site code

5. Limiting values

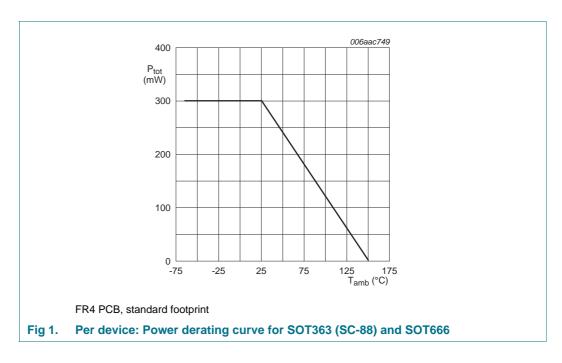
Table 6. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Min	Max	Unit
Per transis	stor				
V_{CBO}	collector-base voltage	open emitter	-	-50	V
V_{CEO}	collector-emitter voltage	open base	-	-50	V
V_{EBO}	emitter-base voltage	open collector	-	-6	V
V_{I}	input voltage				
	positive		-	+6	V
	negative		-	-40	V
Io	output current		-	-100	mA
I _{CM}	peak collector current	single pulse; $t_p \le 1 \text{ ms}$	-	-100	mA
P _{tot}	total power dissipation	$T_{amb} \le 25 ^{\circ}C$			
	PEMB9 (SOT666)		[1][2] _	200	mW
	PUMB9 (SOT363)		<u>[1]</u> -	200	mW
Per device)				
P _{tot}	total power dissipation	$T_{amb} \le 25 ^{\circ}C$			
	PEMB9 (SOT666)		[1][2] _	300	mW
	PUMB9 (SOT363)		<u>[1]</u> -	300	mW
Tj	junction temperature		-	150	°C
T _{amb}	ambient temperature		-65	+150	°C
T _{stg}	storage temperature		-65	+150	°C

^[1] Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated and standard footprint.

^[2] Reflow soldering is the only recommended soldering method.



6. Thermal characteristics

Table 7. Thermal characteristics

Symbol	Parameter	Conditions	ditions Min		Max	Unit
Per transistor						
$R_{th(j-a)}$	thermal resistance from junction to ambient	in free air				
	PEMB9 (SOT666)		[1][2]	-	625	K/W
	PUMB9 (SOT363)		<u>[1]</u> _	-	625	K/W
Per device						
$R_{th(j-a)}$	thermal resistance from junction to ambient	in free air				
	PEMB9 (SOT666)		[1][2] -	-	417	K/W
	PUMB9 (SOT363)		<u>[1]</u> _	-	417	K/W

^[1] Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.

^[2] Reflow soldering is the only recommended soldering method.

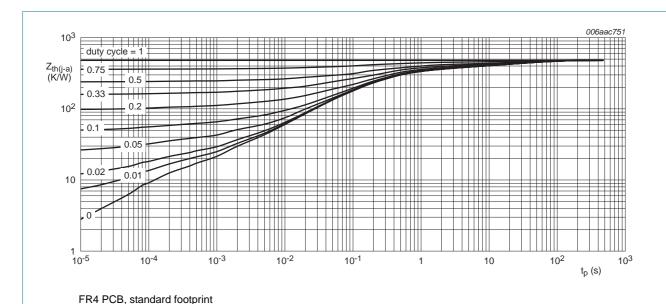


Fig 2. Per transistor: Transient thermal impedance from junction to ambient as a function of pulse duration for

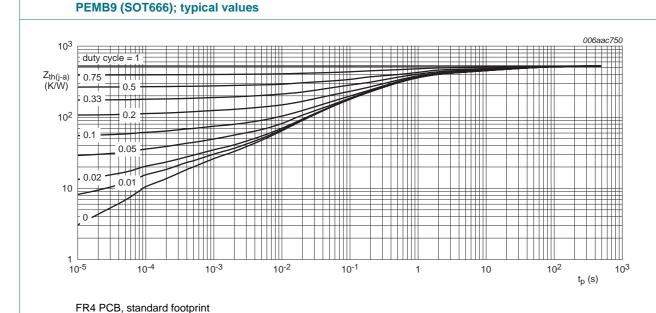


Fig 3. Per transistor: Transient thermal impedance from junction to ambient as a function of pulse duration for PUMB9 (SOT363); typical values

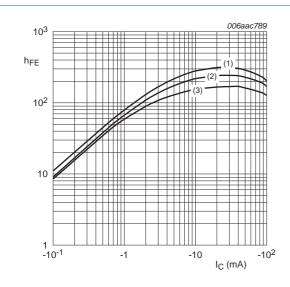
7. Characteristics

Table 8. Characteristics

 $T_{amb} = 25$ °C unless otherwise specified.

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Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Per trans	istor					
I _{CBO}	collector-base cut-off current	$V_{CB} = -50 \text{ V}; I_E = 0 \text{ A}$	-	-	-100	nA
I _{CEO}	collector-emitter cut-off	$V_{CE} = -30 \text{ V}; I_{B} = 0 \text{ A}$	-	-	-1	μΑ
	current	$V_{CE} = -30 \text{ V}; I_{B} = 0 \text{ A};$ $T_{j} = 150 ^{\circ}\text{C}$	-	-	-5	μА
I _{EBO}	emitter-base cut-off current	$V_{EB} = -5 \text{ V}; I_C = 0 \text{ A}$	-	-	-150	μА
h _{FE}	DC current gain	$V_{CE} = -5 \text{ V}; I_C = -5 \text{ mA}$	100	-	-	
V _{CEsat}	collector-emitter saturation voltage	$I_C = -5 \text{ mA}; I_B = -0.25 \text{ mA}$	-	-	-100	mV
$V_{I(off)}$	off-state input voltage	$V_{CE} = -5 \text{ V}; I_{C} = -100 \mu\text{A}$	-	-0.7	-0.5	V
V _{I(on)}	on-state input voltage	$V_{CE} = -0.3 \text{ V}; I_{C} = -1 \text{ mA}$	-1.4	-0.8	-	V
R1	bias resistor 1 (input)		7	10	13	kΩ
R2/R1	bias resistor ratio		3.7	4.7	5.7	
C _c	collector capacitance	$V_{CB} = -10 \text{ V}; I_E = i_e = 0 \text{ A};$ f = 1 MHz	-	-	3	pF
f _T	transition frequency	$V_{CE} = -5 \text{ V}; I_{C} = -10 \text{ mA};$ [1] $f = 100 \text{ MHz}$	-	180	-	MHz

^[1] Characteristics of built-in transistor



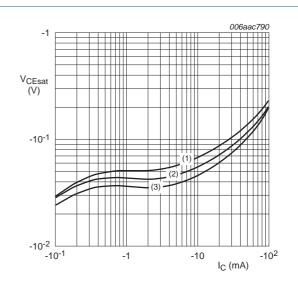
$$V_{CE} = -5 \text{ V}$$

(1)
$$T_{amb} = 100 \, ^{\circ}C$$

(2)
$$T_{amb} = 25 \, ^{\circ}C$$

(3) $T_{amb} = -40 \, ^{\circ}C$

Fig 4. DC current gain as a function of collector current; typical values



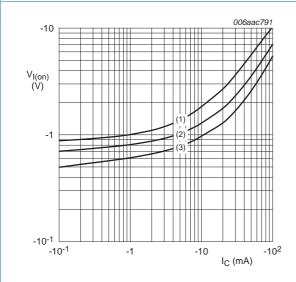
$$I_{\rm C}/I_{\rm B} = 20$$

(1)
$$T_{amb} = 100 \, ^{\circ}C$$

(2)
$$T_{amb} = 25 \, ^{\circ}C$$

(3)
$$T_{amb} = -40 \, ^{\circ}C$$

Fig 5. Collector-emitter saturation voltage as a function of collector current; typical values



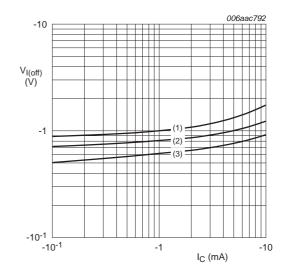
$$V_{CE} = -0.3 \text{ V}$$

(1)
$$T_{amb} = -40 \, ^{\circ}C$$

(2)
$$T_{amb} = 25 \, ^{\circ}C$$

(3) $T_{amb} = 100 \, ^{\circ}C$

Fig 6. On-state input voltage as a function of collector current; typical values



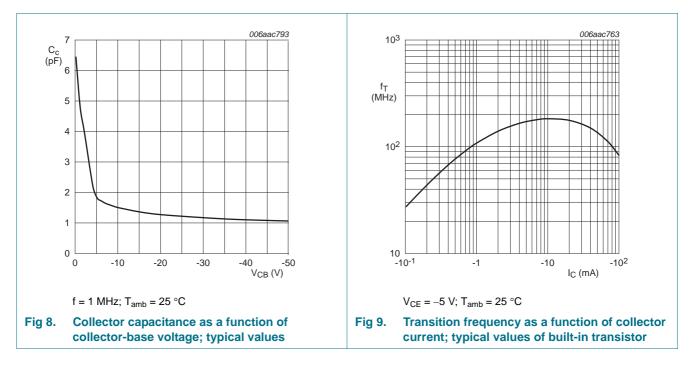
$$V_{CE} = -5 \text{ V}$$

(1)
$$T_{amb} = -40 \, ^{\circ}C$$

(2)
$$T_{amb} = 25 \, ^{\circ}C$$

(3) $T_{amb} = 100 \, ^{\circ}C$

Fig 7. Off-state input voltage as a function of collector current; typical values

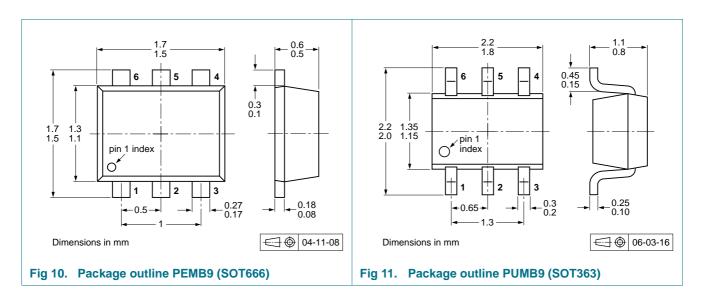


8. Test information

8.1 Quality information

This product has been qualified in accordance with the Automotive Electronics Council (AEC) standard *Q101 - Stress test qualification for discrete semiconductors*, and is suitable for use in automotive applications.

9. Package outline



PEMB9_PUMB9

10. Packing information

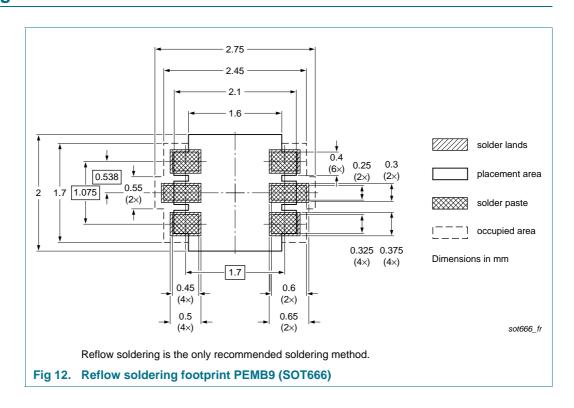
Table 9. Packing methods

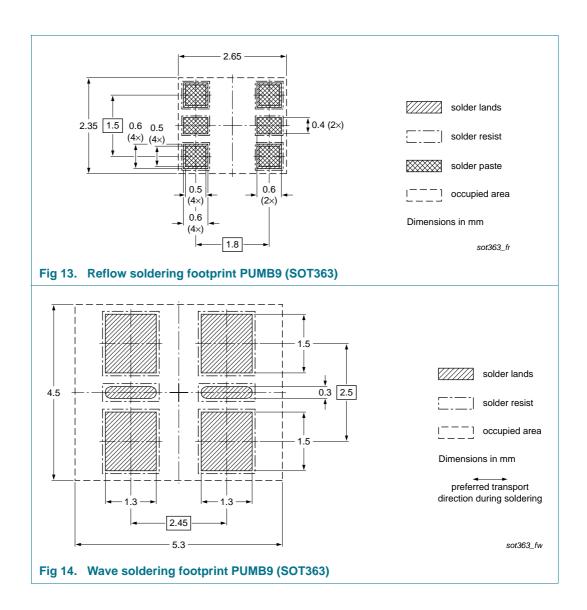
The indicated -xxx are the last three digits of the 12NC ordering code.[1]

		0					
Type Pa	Package	Description		Packing quantity			
				4000	8000	10000	
PEMB9 SOT666	2 mm pitch, 8 mm tape and reel	-	-	-315	-		
		4 mm pitch, 8 mm tape and reel	-	-115	-	-	
PUMB9 S	SOT363	4 mm pitch, 8 mm tape and reel; T1	-115	-	-	-135	
		4 mm pitch, 8 mm tape and reel; T2	-125	-	-	-165	

- [1] For further information and the availability of packing methods, see Section 14.
- [2] T1: normal taping
- [3] T2: reverse taping

11. Soldering





12. Revision history

Table 10. Revision history

Document ID	Release date	Data sheet status	Chango notice	Supercodes			
	11010000		Change notice	Supersedes			
PEMB9_PUMB9 v.3	20111122	Product data sheet	-	PEMB9_PUMB9 v.2			
Modifications:	 The format of this document has been redesigned to comply with the new identity guidelines of NXP Semiconductors. 						
	 Legal texts 	 Legal texts have been adapted to the new company name where appropriate. 					
	Section 1 "Product profile": updated						
	Section 4 "Marking": updated						
	• Figure 1 to 9: added						
	Section 5 "Limiting values": updated						
	Section 6 "Thermal characteristics": updated						
	 Table 8 "Characteristics": V_{i(on)} redefined to V_{I(on)} on-state input voltage, V_{i(off)} redefined to V_{I(off)} off-state input voltage, I_{CEO} updated, f_T added 						
	Section 8 "	Test information": added					
	Section 9 "Package outline": superseded by minimized package outline drawings						
	Section 10 "Packing information": added						
	Section 11 "Soldering": added						
	Section 13 "Legal information": updated						
PEMB9_PUMB9 v.2	20031003	Product data sheet	-	PUMB9 v.1 PEMB9 v.1			
PUMB9 v.1	20030203	Objective specification	-	-			
PEMB9 v.1	20030107	Product specification	-	-			

13. Legal information

13.1 Data sheet status

Document status[1][2]	Product status[3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

- [1] Please consult the most recently issued document before initiating or completing a design
- [2] The term 'short data sheet' is explained in section "Definitions"
- [3] The product status of device(s) described in this document may have changed since this document was published and may differ in case of multiple devices. The latest product status information is available on the Internet at URL http://www.nxp.com.

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PEMB9_PUMB9

PEMB9; PUMB9

PNP/PNP resistor-equipped transistors; R1 = 10 k Ω , R2 = 47 k Ω

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